

## Plastic-Encapsulate Transistors

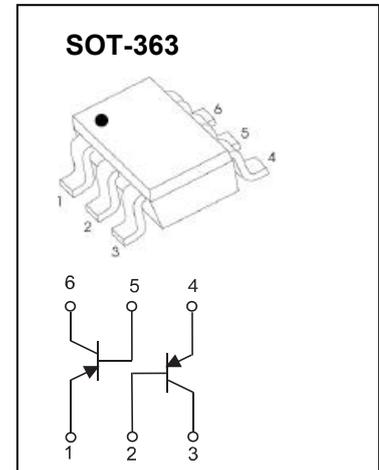
TRANSISTOR (PNP)

### FEATURES

- Complementary to MMDT9014DW
- MARKING: TGM6

### MAXIMUM RATINGS ( $T_a=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
$V_{CB0}$	Collector-Base Voltage	-50	V
$V_{CEO}$	Collector-Emitter Voltage	-45	V
$V_{EBO}$	Emitter-Base Voltage	-5	V
$I_C$	Collector Current	-100	mA
$P_C$	Collector Power Dissipation	200	mW
$R_{\theta JA}$	Thermal Resistance From Junction To Ambient	625	$^{\circ}\text{C}/\text{W}$
$T_j$	Junction Temperature	150	$^{\circ}\text{C}$
$T_{stg}$	Storage Temperature	-55~+150	$^{\circ}\text{C}$



### ELECTRICAL CHARACTERISTICS ( $T_a=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CB0}$	$I_C = -100\mu\text{A}, I_E = 0$	-50			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -0.1\text{mA}, I_B = 0$	-45			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -100\mu\text{A}, I_C = 0$	-5			V
Collector cut-off current	$I_{CB0}$	$V_{CB} = -50\text{V}, I_E = 0$			-0.1	$\mu\text{A}$
Emitter cut-off current	$I_{EBO}$	$V_{EB} = -5\text{V}, I_C = 0$			-0.1	$\mu\text{A}$
DC current gain	$h_{FE}$	$V_{CE} = -5\text{V}, I_C = -1\text{mA}$	300		400	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -100\text{mA}, I_B = -10\text{mA}$			-0.3	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -100\text{mA}, I_B = -10\text{mA}$			-1	V
Base-emitter saturation voltage	$V_{BE}$	$V_{CE} = -5\text{V}, I_B = -2\text{mA}$	-0.6		-0.75	V
Transition frequency	$f_T$	$V_{CE} = -5\text{V}, I_C = -10\text{mA}$ $f = 30\text{MHz}$	150			MHz

## Typical Characteristics

Static Characteristic

